Test Org.*	Device	Function	Technology	Mfr.	Effective SEU LET* Threshold	Device Xsection (cm^2)	Bits Tested	Bit Xsection (cm^2)	Test Date	LUth	LU Xsection (cm^2)	Fac.	Remarks 23-Aug-99
		PROMs											
	Note: Entries in **RED** indicate data added since the 1997 Compendium.												
JPL	93451	(Fusible link)	Bipolar STTL	FAS	>37				Jan-88	>104		BNL	Corrects prior data.
JPL	2764A	8K x 8	NMOS	INT	<17	1.5E-03				>120		BNL	
JPL/ARSP	27C64	8K x 8	CMOS	INT					Mar-88	14	1.0E-04	BNL	Also tested @ UCB.
MMS	82HS641	8K x 8	Bipolar	SGN	31	7.0E-06			1992	>32		GANIL	Dufour, et al, 92IEEE Wrkshp Rec., pg 21.
GSFC	82HS641A	8K x 8	Bipolar	SGN	>73				Dec-91	>73		BNL	Compare to GANIL data above.
ARSP	AM27S49A	8K x 8	Bipolar TTL	AMD	7	9.0E-05			Dec-89			UCB	No permanent errors. Errors for read cycle only.
BREL	CY7C261	8K x 8	CMOS	CYP	<15				1995	<15	7.0E-04	UCB?	Normand et al, 95IEEE Wrkshp Rec., pg 33.
MMS	CY7C261-55	8K x 8	CMOS	CYP	<32	2.0E-01			1992	<32	5.0E-04	GANIL	Dufour, et al, 92IEEE Wrkshp Rec., pg 21.
JPL	HM6611	32 x 32	CMOS	HAR					1983	45	1.0E-04	UCB	Soliman & Nichols, 83IEEE TNS, No. 6, pg 4514.
JPL	HM6616	2K x 8	CMOS/epi (12 µm)	HAR	<37	1.0E-02			May-87	40		UCB	
JPL/CNES	HM6617	2K x 8	CMOS/epi (7 µm)	HAR	12	7.0E-05			Dec-87				
GD	HM6617	2K x 8	CMOS/epi	HAR		3.0E-06			Nov-87			Cf-252	Output buffer upsets.
MMS	HM6617	2K x 8	CMOS	HAR	32	3.0E-04			1992	58	2.0E-04	GANIL	Dufour, et al, 92IEEE Wrkshp Rec., pg 21.
JPL/HAR/ ARSP	HM6641	512 x 8	CMOS	HAR	22				1983	42	1.0E-04	UCB	Soliman & Nichols, 83IEEE TNS, No. 6, pg 4514.
JPL	HS1-6617RH-8	2K x 8	CMOS/epi	HAR	19	2.0E-05			Oct-90	>120			Address register upsets only. Compare to HM6617.
JPL	HS6616 (rad hard)	2K x 8	CMOS/epi	HAR					Jun-87	>120			At T=120 deg. C.
	HS-6664RH	8K x 8	CMOS, TSOS-4 process	HAR	116				1994	>116		BNL	Au at 45 deg angle. Harris Space Product News, 3rd Q, 1994
MMS	MB7144E	8K x 8	Bipolar	FUJ					1992	>140		GANIL	Dufour, et al, 92IEEE Wrkshp Rec., pg 21.
ROCK	R29791	8K x 8	Bipolar	RAY	15	2.4E-05			Apr-93	>74		BNL	Upsets are transients at output; no lost data.
MMS	R29793	8K x 8	Bipolar	RAY	8	3.0E-05			1992	>87		GANIL	Dufour, 92IEEE Wrkshp Rec., pg 21.. Peripherals only.
LIN	R29793	8K x 8	Bipolar Fuse link	RAY					1991	>164		BNL	Sferrino '91
	UT28F64	8K x 8 (antifuse-based)	CMOS	UTM					Jul-96	>128			Anthony Jordan, UTMC News

Heavy Ion SEE

Test Org.*	Device	Function	Technology	Mfr.	Effective SEU LET* Threshold	Device Xsection (cm^2)	Bits Tested	Bit Xsection (cm^2)	Test Date	LUth	LU Xsection (cm^2)	Fac.	Remarks 23-Aug-99
Legend													
	Manufacturers: AMD - Advanced Micro Devices; CYP - Cypress Semiconductors; FAS - Fairchild Semiconductor Division; FUJ - Fujitsu; HAR - Harris Corp; INT - Intel; SGN - Signetics Corp;												
	RAY - Raytheon; UTM - United Technologies Microelectronic Center												
	Test Organizations			**Radiation Test Facilities**									
	ARSP - Aerospace Corp., El Segundo, CA			BNL - Tandem Van de Graaff, Brookhaven National Laboratories, Long Island, NY									
	BREL - Boeing Radiation Effects Laboratory, Seattle, WA			Cf-252 - Cf-252 Fission Source (various facilities)									
	CNES - Centre National d'etudes Spatiales, Toulouse, France			GANIL - GANIL Accelerator, France									
	GD - General Dynamics, Azuza, CA			UCB - 88-inch Cyclotron, University of California, Berkeley, CA									
	GSFC - Goddard Space Flight Center, Greenbelt, MD												
	HAR - Harris Corp, Melbourne, FL												
	JPL - Jet Propulsion Laboratory, Pasadena, CA												
	LIN - MIT Lincoln Labs, Lexington, MA												
	MMS - Matra Marconi Space, France												
	ROCK - Rockwell Corp. (now Boeing), Anaheim, CA												